



#10/B
3-19-01
all

PATENT
740756-1914

TECHNOLOGY CENTER 2800
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:

Shunpei YAMAZAKI et al.

Application No.: 09/235,770

Filed: January 25, 1999

For: SEMICONDUCTOR DEVICE
AND METHOD FOR FORMING
THE SAME

) Art Unit: 2813

) Examiner: L. Schillinger

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on MARCH 7, 2001.

John F. Antrell

AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

March 7, 2001

Dear Sir:

In response to the Examiner's non-final Office Action mailed September 7, 2000, the period for responding having been extended Three (3) months, please consider the following amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please amend claim 15 as follows:

- B'
15. (Amended) A CMOS semiconductor device having an N-channel type thin film transistor and a P-channel type thin film transistor, each of which comprising:
- a first insulating film comprising silicon nitride formed on a substrate;
 - a second insulating film comprising silicon oxide formed on said first insulating film;
 - a semiconductor layer formed on said second insulating film wherein said semiconductor layer includes at least source, drain and channel regions;
 - a third insulating film comprising silicon oxide formed on said semiconductor layer;